

L Number	Hits	Search Text	DB	Time stamp
1	296	"4544887" "4558660" "4581578" "4599558" "4871417" "5306671" "5453702" "5470799" "5471293" "5663657" "5661408" "5716495"	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/06/24 15:00
2	5	("4544887" "4558660" "4581578" "4599558" "4871417" "5306671" "5453702" "5470799" "5471293" "5663657" "5661408" "5716495") and (semiconductor near4 (surface adj treatment))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/06/24 15:01
-	609	semiconductor near4 (surface adj treatment)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/06/22 14:45
-	661	semiconductor near4 (surface adj treatment)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/06/24 15:01
-	308	(semiconductor near4 (surface adj treatment)) and wafer	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/06/22 14:45
-	3	((semiconductor near4 (surface adj treatment)) and wafer) and (inversion adj condition)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/06/23 15:01
-	3	((semiconductor near4 (surface adj treatment)) and wafer) and (IR or infrared)) and (inversion adj condition)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/06/23 11:53
-	4	((semiconductor near4 (surface adj treatment)) and wafer) and (IR or infrared)) and (desorb or desorption)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/06/23 11:51
-	7	("3850508" "4824698" "5216362" "5581194" "5977788" "61685716326220041")	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/06/23 11:52
-	3	((semiconductor near4 (surface adj treatment)) and (IR or infrared)) and (inversion adj condition)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/06/23 11:54
-	5	(semiconductor near4 (surface adj treatment)) and (inversion adj condition)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/06/23 12:28
-	28	((semiconductor near4 (surface adj treatment)) and wafer) and (IR or infrared)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/06/23 15:03
-	5	(semiconductor near6 (surface adj treatment)) and (inversion adj condition)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/06/23 13:03
-	5	(semiconductor near4 (surface adj treatment)) and (inversion adj condition)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/06/23 15:02
-	21	(semiconductor near4 (surface adj treatment)) and (electron adj hole)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/06/23 15:02

-	11	(semiconductor near4 (surface adj treatment)) and (electron adj hole adj pair)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/06/23 15:03
-	6	((semiconductor near4 (surface adj treatment)) and (electron adj hole adj pair)) and (IR or infrared)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/06/23 15:04